

September 23-26, 2019 Santa Clara, CA

Emerging Memory Update 2019: What a Difference a Year Makes!

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What A Difference A Year Makes!



- Emerging Memory Update by Type
- Emerging Memory Support Update
- Hurdles & Outlook



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Emerging Memory Types

- PCM/XPoint
- MRAM
- ReRAM
- FRAM
- Others

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PCM/3D XPoint – "Optane"



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3D XPoint Must Be Priced Below DRAM Otherwise People will Just Buy DRAM



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Intel Incurring Significant XPoint Losses SD@



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Meanwhile, DRAM Prices are Collapsing SD©





- Optane SSDs gaining modest acceptance
 - NAND makers countering with fast SLC SSDs
- Optane DIMMs key selling point for nextgeneration server CPUs

3D XPoint Report

- 2019 Update from Objective Analysis
- The Why, How, and When of 3D XPoint Memory
 - Why Intel wants it
 - How it fits into the memory hierarchy
 - Impact on DRAM
 - When will it sell in volume
- Detailed Forecasts

https://Objective-Analysis.com/reports/#XPoint

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July 2019

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Magnetic RAM: MRAM



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Three MRAM Types: Toggle, STT, & SOT SD®

Toggle Mode (legacy)



Magnets unaligned =

High resistance. "1"

Spin Transfer Torque (STT, ramping)



Spin-Orbit Torque MRAM (future)

Spin-Orbit Torque (SOT)



Higher reliability in-plane currentSOT switching faster than STT

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MRAM Status

- MRAM cache in IBM SSDs
- Spin Memory (Spin Torque Technologies) launches:
 - Precessional Spin Current
 - Endurance Engine Technologies
- All major foundries sampling MRAM, two shipping
- Everspin still sole supplier of stand-alone MRAMs
 - Over 123 million units shipped
 - Avalanche is sampling
- Today's markets: Space, high-uptime systems, caches and buffers

Embedded MRAM (1)



- MRAM will shrink past SRAM & flash
- Tuned to application
 - Retention
 - Endurance
 - Capacity

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Embedded MRAM (2)

- 1T/2T MRAM smaller than 6T SRAM
- NOR flash scaling limit ≤15nm
- MRAM could replace embedded SRAM & NOR
 - Lower power
 - Lower cost
 - Higher density



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MRAM Foundry Developments

- All major semiconductor foundries involved
 - Samsung, TSMC, Global Foundries, UMC...
- Many plan to cost reduce
 - Moving from BEOL to front end
- MRAM needs new tools
 - Drives more capital spending

Resistive RAM: ReRAM

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Many Flavors of ReRAM

- CMOx
- CBRAM
- PCM
- Memristor
- Carbon nanotubes

All use the value of a resistance to represent a "1" or "0"

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Two ReRAM Types in the Lead

- SiO₂-based
 - Crossbar, Weebit Nano
 - Positioned as the memory for neural networks
 - Crossbar production at SMIC
 - Not yet in volume
- Metal filament
 - Adesto in volume production

Ferroelectrics: FRAM



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- Ramtron (Now Cypress)
 - Sole supplier of stand-alone FRAM
 - PZT Lead Zirconium Titanate
- Other renditions:
 - Thinfilm, organic FRAMs
 - Symetrix IP provider
- New HfO₂ approach from NamLab, Dresden
 - Uses well-understood materials (Hafnium Oxide)
- Today's markets:
 - RFID, other low write current applications

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23

All New Memories Share Some Attributes SD@

- Small single-element cell
 - Supports small/inexpensive die and 3D stacking
 - Promises to scale past DRAM & NAND flash
- Write in place
 - No "Block Erase"
 - More symmetrical read/write speeds
- Nonvolatile/Persistent
 - These can <u>all</u> be used as Persistent Memory: "PM"

Memory Attributes By Technology

	Units	SRAM	DRAM	NOR Flash	NAND Flash	Toggle MRAM	ST-MRAM	FRAM	РСМ	RRAM
Byte Read Time	ns	2	10	25	10,000	35	<10	55	16	10
Byte Write Time	ns	2	10	5,000,000	200,000	35	<10	55	30	10
Standby Current	mA	<	45	<	<	<	<	<	<	<1
Read Current	mA	20	220	20	25	30	15	<10	15	15
Write Current	mA	20	240	50	25	30	15	<10	20	20
Endurance	P/E Cycles	Infinite	Infinite	10 ⁵	104	1011	1013	1014	106	106
Retention	Yrs @ 55°C	0	10-9	>10	>10	>20	>20	>10	>10	>10
Scaling Limit	nm	5	10?	45?	14	65	5	5	5	5
Cell Size	f²	50	6-8	6-8	4 effective with MLC	35-40	8-9	8-20	4	4
Select Device	N/A	Transistor	Transistor	Transistor	Transistor	Transistor	Transistor	Transistor	Diode	Diode
MLC Capability	Bits/ Cell	I	I	2	4	2	4	I	4	TBD
SEU Immune	N/A	No	No	No	No	Yes	Yes	No	Yes	Yes
SEL Immune	N/A	No	No	No	No	Yes	Yes	No	Yes	Yes
TID	krad (Si)	<100	<100	<100	<100	>1,000	>1,000	<100	>1,000	>1,000

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- Emerging Memory Update by Type
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Support Requirements

- Hardware advancements (JEDEC, Others)
 - Supporting early development
 - Ongoing requirements
- Software support (SNIA)
 - O/S support
 - Application program support
- EDA support

Hardware: Early Development

- Early groundwork has been helpful
 - NVDIMM-N
 - DRAM with flash backup
 - BIOS changes
 - Boot without reloading memory
 - New power fail signal brought to DIMM
- 3D XPoint driving changes

Design Tools MRAM Options

- Embedded MRAM needs EDA support
 - Synopsis support announced for 2Q19
 - Cadence to support MRAM in DDR4 controllers



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NVDIMM MARKET

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NVDIMM Report

- Objective Analysis
- Explains the NVDIMM markets
 - NVDIMM-N
 - NVDIMM-P
- Vendor profiles
- Support requirements
- Market forecast

https://Objective-Analysis.com/reports/#NVDIMM

Ongoing Hardware Requirements

- Nonuniform Memory Architecture: "NUMA"
- MMU Redesign
- Faster context switches needed
 - Use polling for now
- Updated DDR4 bus
 - Support for non-deterministic access times

Software: Operating System Support

- SNIA's Persistent Memory Programming Model
 - https://www.SNIA.org/PM



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Software: Application Program Support SD@

- PM is useless if its advantage is untapped
 - Persistence is unknown in most software
- This change will take some time
 - Closed systems can use it now
 - Hyperscale Data Centers, SANs
 - Open systems will evolve

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The Vision: Replace Existing Technologies

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Manufacturers shrink processes to drive this

This is Moore's Law in Action!

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NAND \$/GB >DRAM's Until 2004

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In 2004 NAND GB ¹/₃ of DRAM's

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The Same is True of All Memory Technologies

There can be no price advantage without comparable scale

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Outlook 3-26, 2019 Santa Clara, CA

- Nothing works in a vacuum
 - PM is a part of the greater memory ecosystem
 - The memory market swings wildly
- Foundry processes will have a huge impact

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Status of Today's Memory Cycle

- Predicted collapse is well underway
 - Supply-driven overcapacity
 - 3D NAND selling close to cost
 - DRAM still has room to fall
- Won't end until demand catches up with supply
 - Typically this takes 2 years
 - China likely to enter market in 2021

- Persistent memory competes against established technologies
 - Example: 3D XPoint must be cheaper than DRAM
- A DRAM collapse will create an XPoint collapse
 - Even though XPoint is sole-sourced!

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Growth in New Memory Shipments

Embedded MRAM replaces most SoC NOR and SRAM

 Strong appeal in AI apps

Could exceed \$37B by 2029!

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New Memory Capital Spending Increases SD@

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- Emerging Memories Making Good Progress
 - Major commitments for server and embedded applications
 - Still hard to determine the frontrunner
- Support requirements being well addressed
- New memories will drive capital spending
- Many issues confront the market

Questions?

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September 23-26, 2019 Santa Clara, CA

- Technical and Market Analysis
- Consulting
- Reports and Newsletter
 - Emerging Memories Poised to Explode: Emerging Memory Report
 - Digital Storage in Media and Entertainment
 - Digital Storage Technology Newsletter
- Events
 - Emerging Memory and Artificial Intelligence Workshop, Stanford, 8/29/19
 - Storage Valley Supper Club

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Semiconductor Forecast Accuracy

Year	Forecast	Actual
2008	Zero growth at best.	-3%
2009	Growth in the mid teens	-9%
<u>2010</u>	Should approach 30%	32%
<u>2011</u>	Muted revenue growth: 5%	0%
<u>2012</u>	Revenues drop as much as -5%	-2.7%
<u>2013</u>	Revenues increase nearly 10%	4.9%
<u>2014</u>	Revenues up 20%+	9.9%
<u>2015</u>	Revenues up ~10%	-0.2%
<u>2016</u>	Revenues up ~10%	1.1%
<u>2017</u>	Revenues up ~20%	22%
2018	Strong start supports 10+% growth	14%
2019	Semiconductors down -5%	TBD

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